

ST1802HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

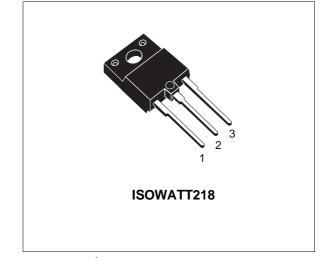
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

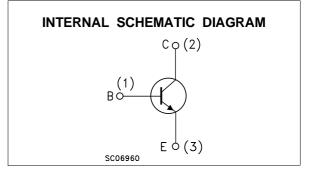
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TV

DESCRIPTION

The ST1802HI is manufactured using collector diffused technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|--|------------|------|
| V _{СВО} | Collector-Base Voltage (I _E = 0) | 1500 | V |
| Vceo | Collector-Emitter Voltage (I _B = 0) | 600 | V |
| V _{EBO} | Emitter-Base Voltage ($I_{C} = 0$) | 7 | V |
| Ι _C | Collector Current | 8 | А |
| Ісм | Collector Peak Current (t _p < 5 ms) | 15 | А |
| Ι _Β | Base Current | 4 | А |
| P _{tot} | Total Dissipation at $T_c = 25 \ ^{\circ}C$ | 50 | W |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| Tj | Max. Operating Junction Temperature | 150 | |

THERMAL DATA

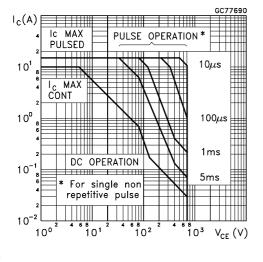
| R _{thj-case} Thermal Resistance Junction-case | Max | 2.5 | °C/W |
|--|-----|-----|------|
|--|-----|-----|------|

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

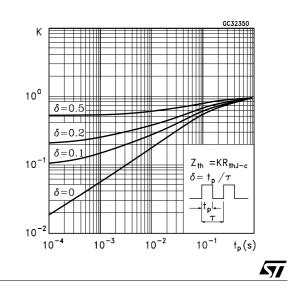
| Symbol | Parameter | Test Conditions | | Min. | Тур. | Max. | Unit |
|----------------------------------|--|---|--|------|----------|----------|----------|
| I _{CES} | Collector Cut-off Current (V _{BE} = 0) | V _{CE} = 1500 V V _{CE} = 1500 V | T _j = 125 ^o C | | | 1 2 | mA mA |
| I _{EBO} | Emitter Cut-off Current $(I_c = 0)$ | V _{EB} = 7 V | | | | 1 | mA |
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | I _C = 100 mA | L = 25 mH | 600 | | | V |
| $V_{CE(sat)^*}$ | Collector-Emitter Saturation Voltage | $I_{C} = 4 A$ $I_{C} = 4 A$ | I _B = 0.8 A I _B = 1.2 A | | | 5 1.5 | V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | I _C = 4.5 A | I _B = 1 A | | | 1.2 | V |
| h _{FE} * | DC Current Gain | $I_{C} = 1 A$ $I_{C} = 5 A$ | V _{CE} = 5 V V _{CE} = 5 V | 4 | 25 | 9 | |
| t _s t _f | INDUCTIVE LOAD Storage Time Fall Time | I _C = 4 A L _B = 5 μH f = 16 KHz | $I_{BON(END)} = 1 A$ $V_{BB} = -2.5 V$ | | 5 0.3 | 6 0.5 | μs μs |

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

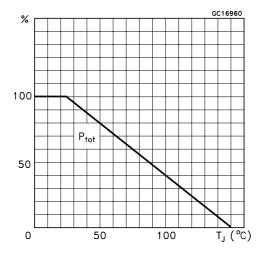
Safe Operating Areas



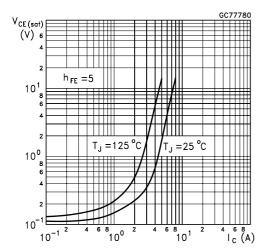
Thermal Impedance



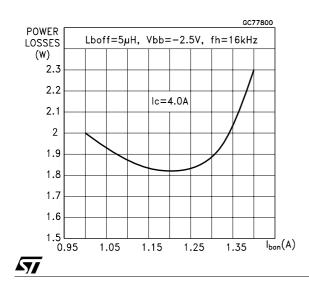
Derating Curve



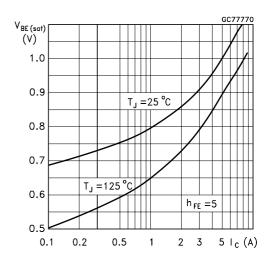
Collector Emitter Saturation Voltage



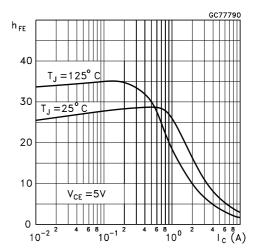
Power Losses At 16 KHz

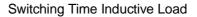


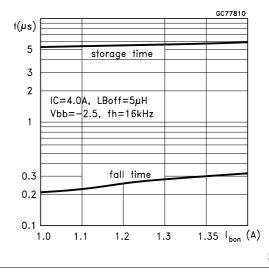
Base Emitter Saturation Voltage



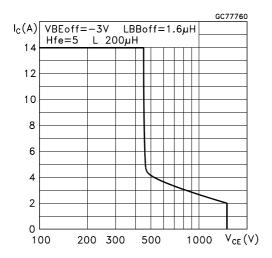
DC Current Gain



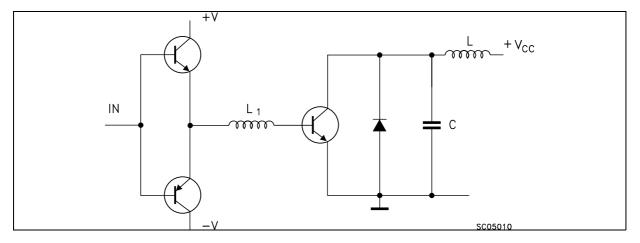




Reverse Biased SOA

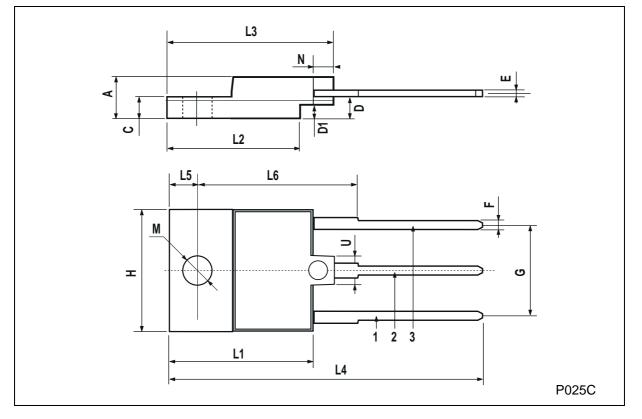


Inductive Load Switching Test Circuits.



| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| А | 5.35 | | 5.65 | 0.210 | | 0.222 |
| С | 3.3 | | 3.8 | 0.130 | | 0.149 |
| D | 2.9 | | 3.1 | 0.114 | | 0.122 |
| D1 | 1.88 | | 2.08 | 0.074 | | 0.081 |
| Е | 0.75 | | 1 | 0.029 | | 0.039 |
| F | 1.05 | | 1.25 | 0.041 | | 0.049 |
| G | 10.8 | | 11.2 | 0.425 | | 0.441 |
| Н | 15.8 | | 16.2 | 0.622 | | 0.637 |
| L1 | 20.8 | | 21.2 | 0.818 | | 0.834 |
| L2 | 19.1 | | 19.9 | 0.752 | | 0.783 |
| L3 | 22.8 | | 23.6 | 0.897 | | 0.929 |
| L4 | 40.5 | | 42.5 | 1.594 | | 1.673 |
| L5 | 4.85 | | 5.25 | 0.190 | | 0.206 |
| L6 | 20.25 | | 20.75 | 0.797 | | 0.817 |
| М | 3.5 | | 3.7 | 0.137 | | 0.145 |
| Ν | 2.1 | | 2.3 | 0.082 | | 0.090 |
| U | | 4.6 | | | 0.181 | |





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